

**2SK3488**

## Ultrahigh-Speed Switching Applications

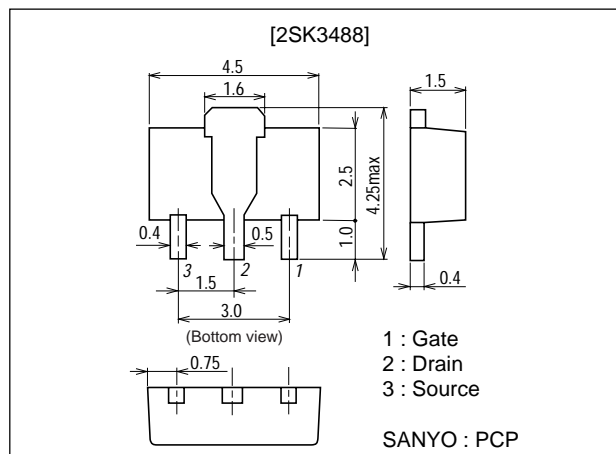
### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

### Package Dimensions

unit : mm

2062A



### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		2.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	10	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (250mm²×0.8mm)	1.0	W
		Tc=25°C	3.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)</sub> DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.3A	1.6	2.3		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =1.3A, V <sub>GS</sub> =10V		125	160	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =0.7A, V <sub>GS</sub> =4V		200	280	mΩ

Marking : LE

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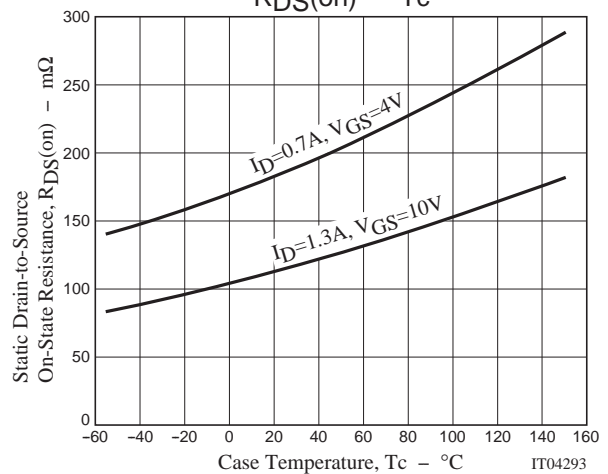
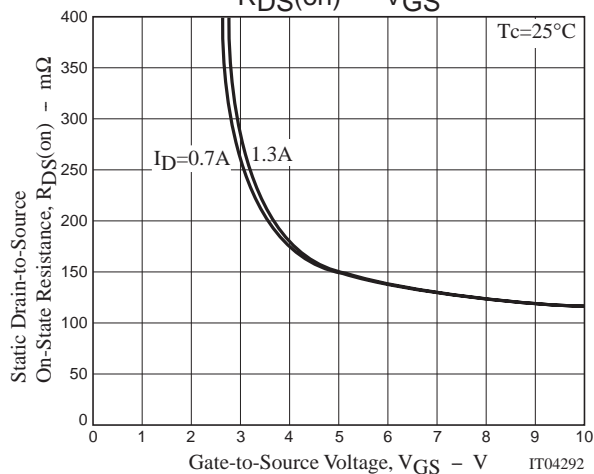
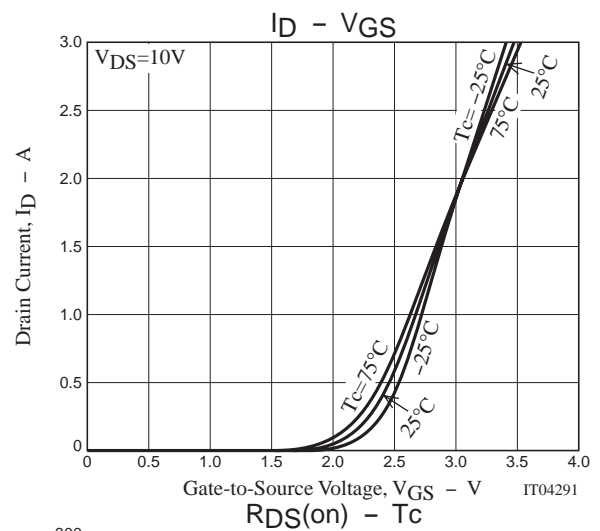
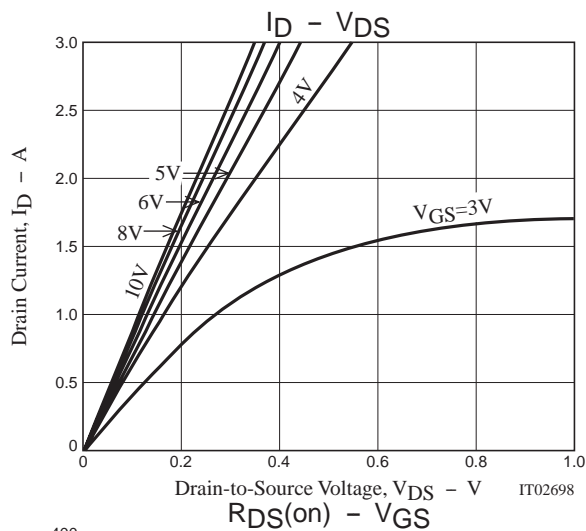
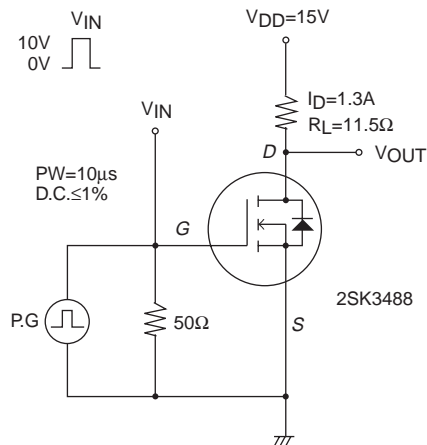
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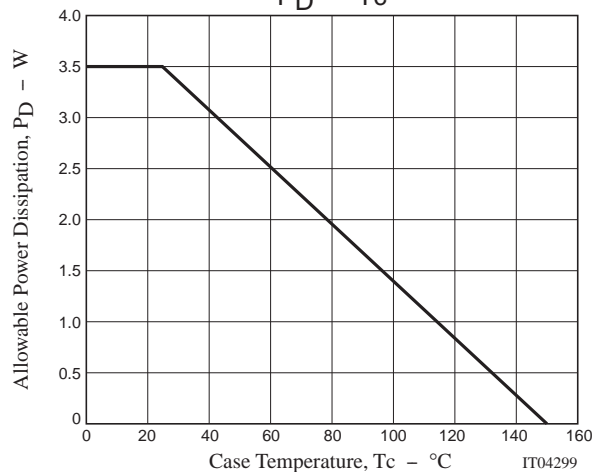
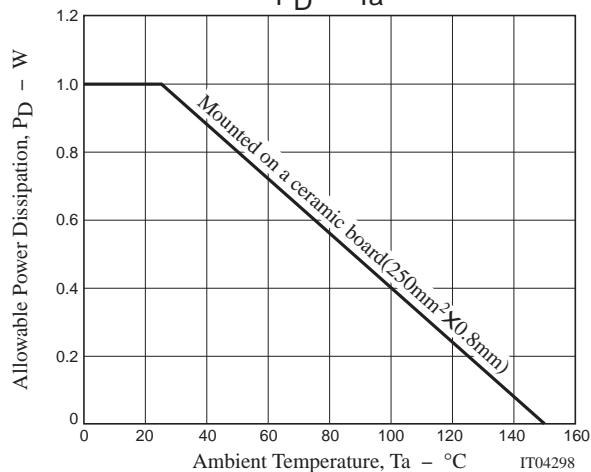
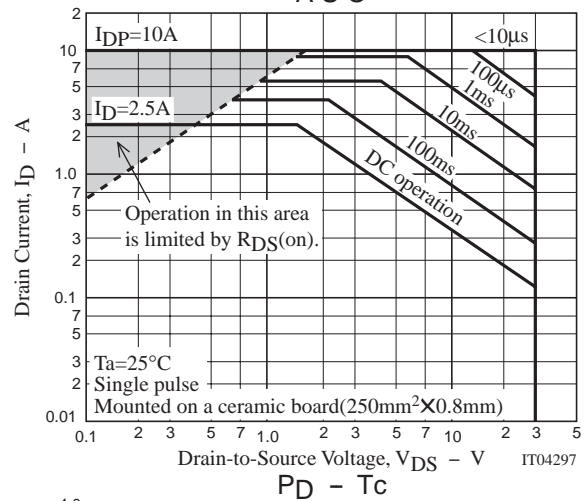
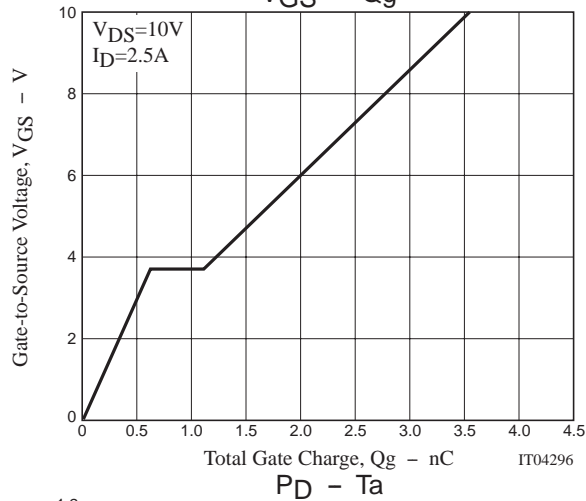
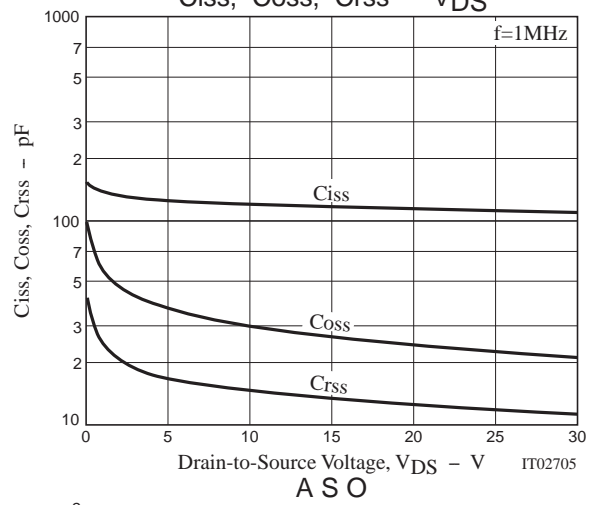
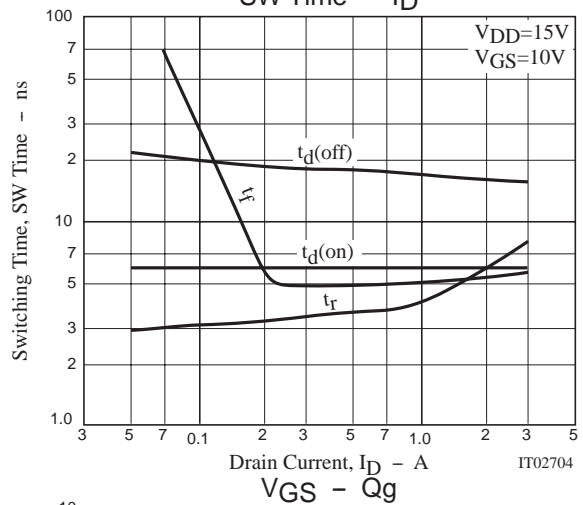
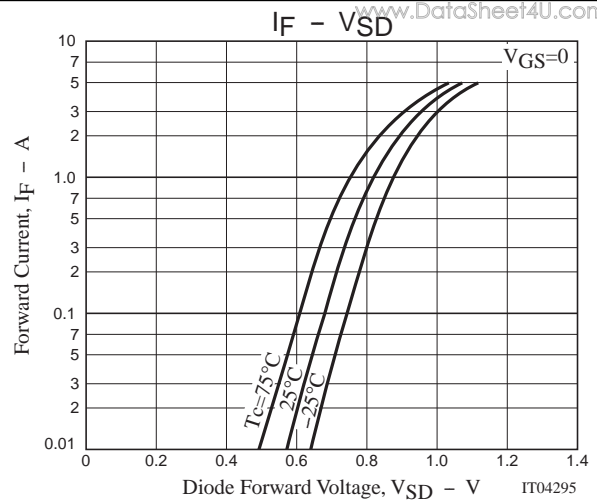
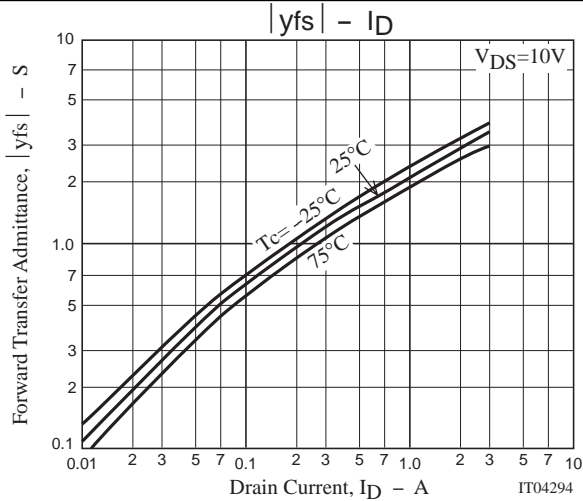
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=10V, f=1MHz$		120		pF
Output Capacitance	$C_{oss}$	$V_{DS}=10V, f=1MHz$		30		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=10V, f=1MHz$		15		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		6		ns
Rise Time	$t_r$	See specified Test Circuit.		5		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		17		ns
Fall Time	$t_f$	See specified Test Circuit.		5		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		3.6		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		0.6		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		0.5		nC
Diode Forward Voltage	$V_{SD}$	$I_S=2.5A, V_{GS}=0$		0.9	1.2	V

**Switching Time Test Circuit**



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